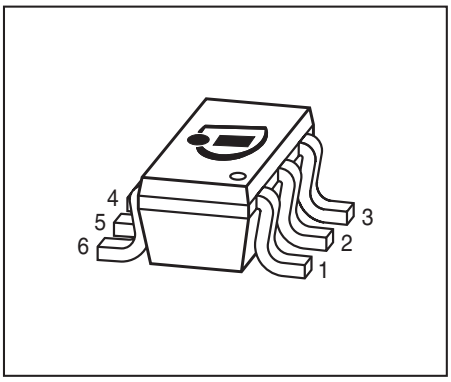
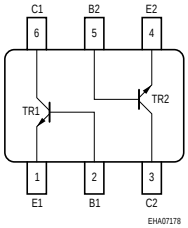
NPN Silicon AF Transistor Array



- For AF stages and driver applications
- High current gain
- Low collector-saturation voltage
- Two (galvanic) internal isolated transistors with good matching in one package
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101

AEC Qualified RoHS



Type	Marking	Pin Configuration						Package
BC817U	6Bs	1=E1	2=B1	3=C2	4=E2	5=B2	6=C1	SC74

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	45	V
Collector-base voltage	V_{CBO}	50	
Emitter-base voltage	V_{EBO}	5	
Collector current	I_C	500	mA
Peak collector current, $t_p \leq 10$ ms	I_{CM}	1000	
Base current	I_B	100	
Peak base current	I_{BM}	200	
Total power dissipation- $T_S \leq 115$ °C	P_{tot}	330	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point[1)]	R_{thJS}	≤ 105	K/W

Electrical Characteristics at T_A = 25°C, unless otherwise specified

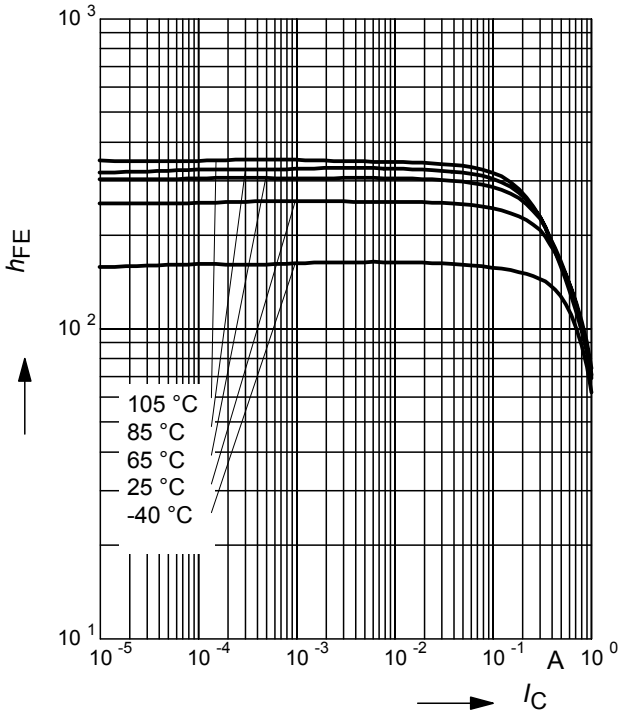
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage I_C = 10 mA, I_B = 0	$V_{(BR)CEO}$	45	-	-	V
Collector-base breakdown voltage I_C = 10 µA, I_E = 0	$V_{(BR)CBO}$	50	-	-	
Emitter-base breakdown voltage I_E = 10 µA, I_C = 0	$V_{(BR)EBO}$	5	-	-	
Collector-base cutoff current V_{CB} = 25 V, I_E = 0 V_{CB} = 25 V, I_E = 0 , T_A = 150 °C	I_{CBO}	 - -	 - -	 0.1 50	µA
Emitter-base cutoff current V_{EB} = 4 V, I_C = 0	I_{EBO}	-	-	100	nA
DC current gain[2)] I_C = 100 mA, V_{CE} = 1 V I_C = 300 mA, V_{CE} = 1 V	h_{FE}	 160 100	 250 -	 400 -	-
Collector-emitter saturation voltage[2)] I_C = 500 mA, I_B = 50 mA	V_{CEsat}	-	-	0.7	V
Base emitter saturation voltage[2)] I_C = 500 mA, I_B = 50 mA	V_{BEsat}	-	-	1.2	
AC Characteristics					
Transition frequency I_C = 50 mA, V_{CE} = 5 V, f = 100 MHz	f_T	-	170	-	MHz
Collector-base capacitance f = 1 MHz, V_{BE} = 10 V	C_{cb}	-	6	-	pF
Emitter-base capacitance V_{EB} = 0.5 V, f = 1 MHz	C_{eb}	-	60	-	

[1]For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation)

[2]Pulse test: t < 300µs; D < 2%

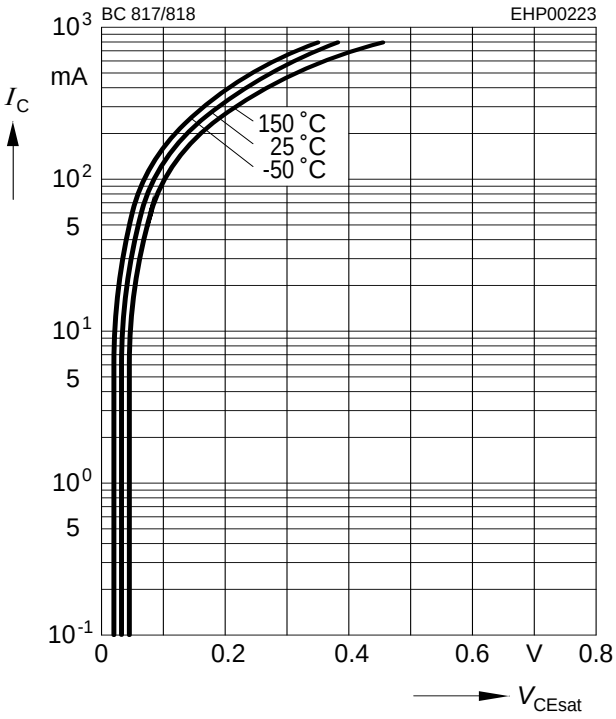
DC current gain $h_{FE} = f(I_C)$

V_{CE} = 1 V



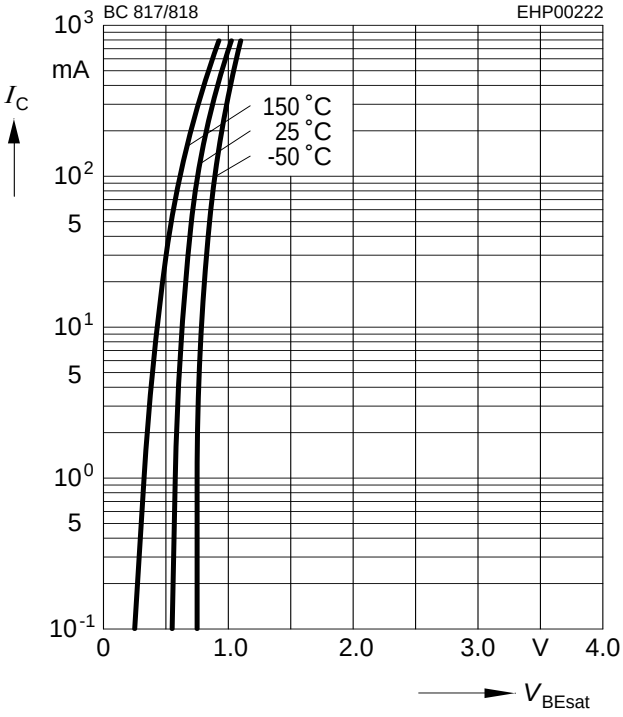
Collector-emitter saturation voltage

$I_C = f(V_{CEsat})$, h_{FE} = 10



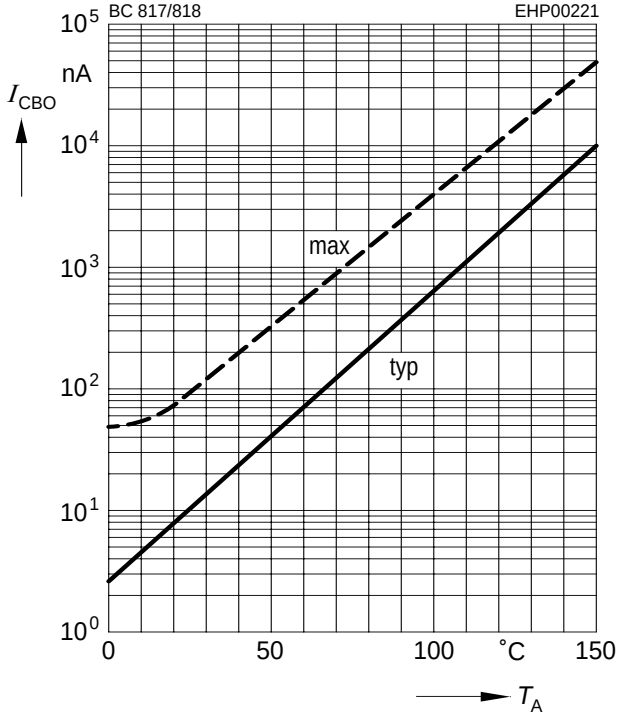
Base-emitter saturation voltage

$I_C = f(V_{BEsat})$, h_{FE} = 10

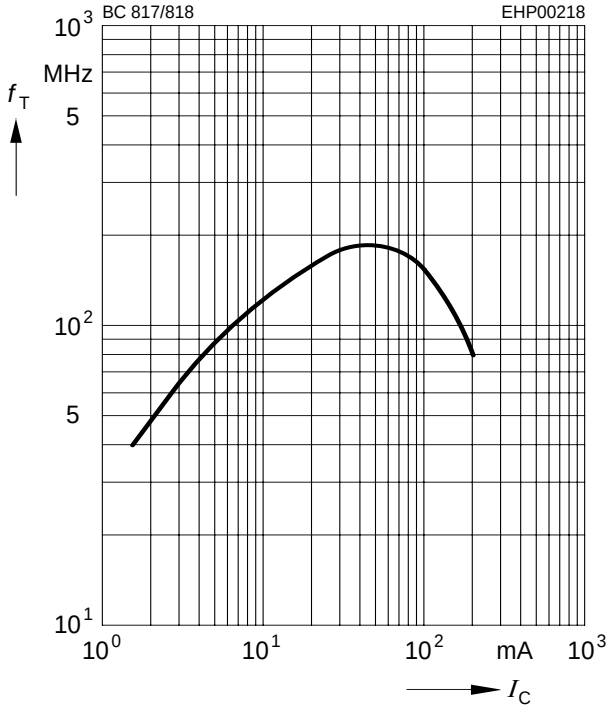


Collector cutoff current $I_{CBO} = f(T_A)$

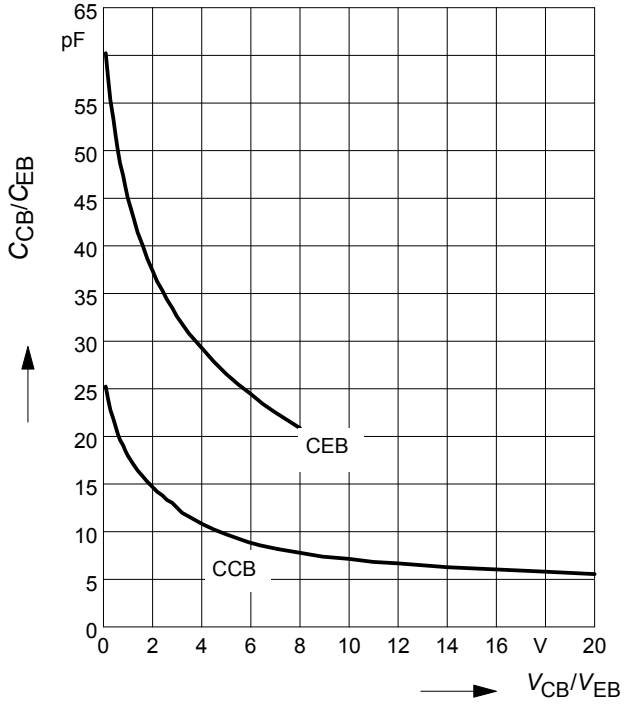
V_{CBO} = 25 V



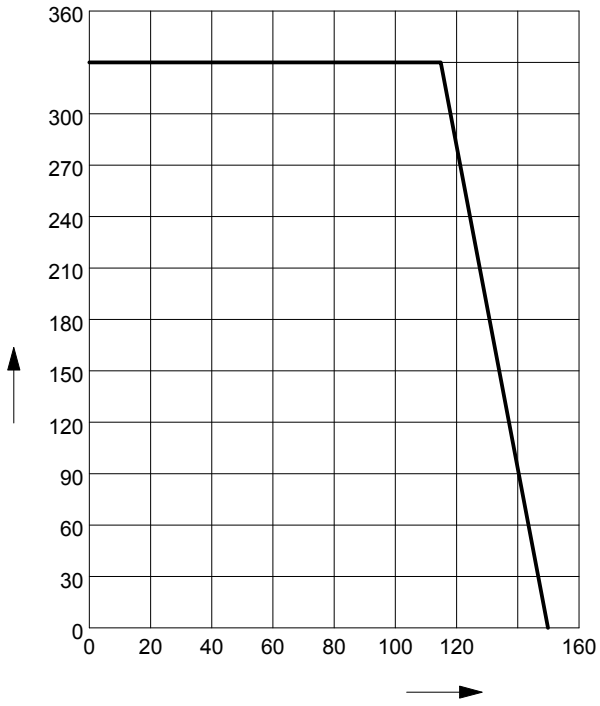
Transition frequency $f_T = f(I_C)$
V_{CE} = parameter in V, f = 2 GHz



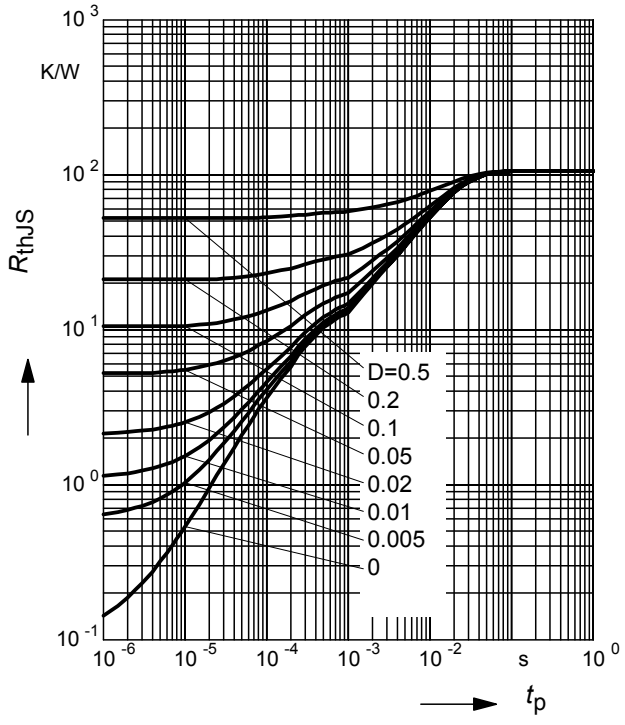
Collector-base capacitance $C_{cb} = f(V_{CB})$
Emitter-base capacitance $C_{eb} = f(V_{EB})$



Total power dissipation $P_{tot} = f(T_S)$

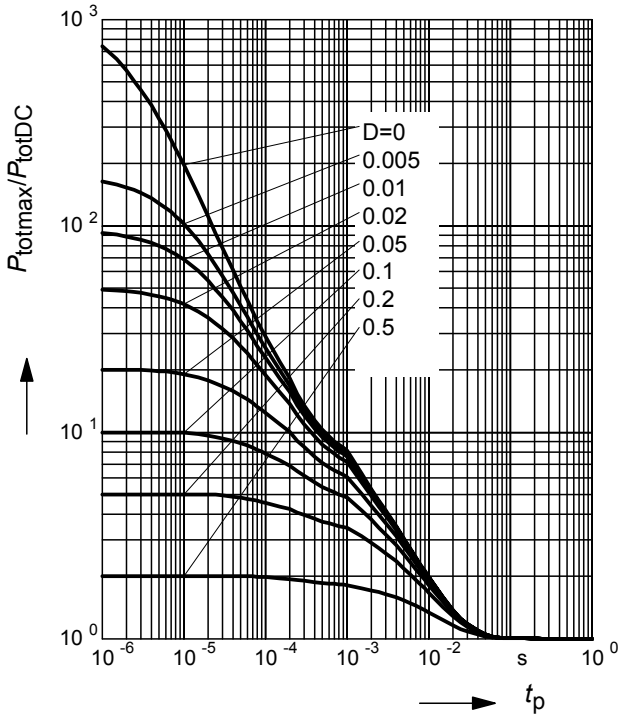


Permissible Pulse Load $R_{thJS} = f(t_p)$

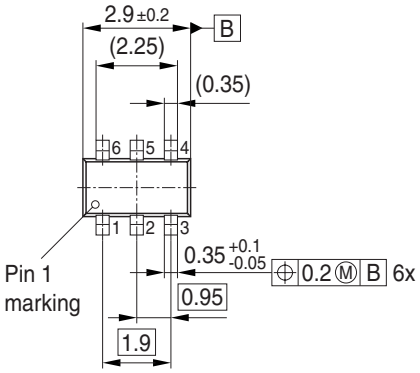


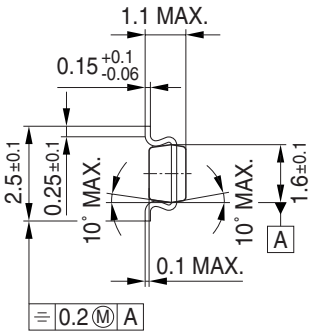
Permissible Pulse Load

$P_{totmax}/P_{totDC} = f(t_p)$

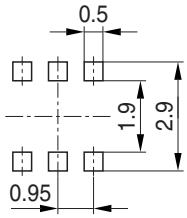


Package Outline



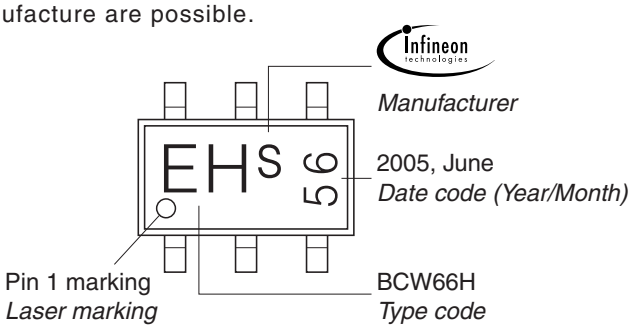


Foot Print



Marking Layout (Example)

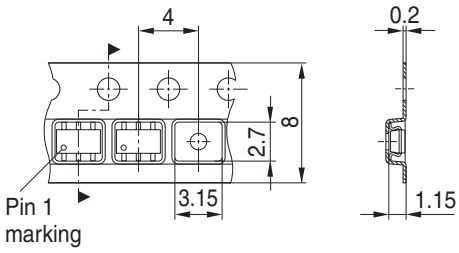
Small variations in positioning of
Date code, Type code and Manufacture are possible.



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel
Reel ø330 mm = 10.000 Pieces/Reel

For symmetric types no defined Pin 1 orientation in reel.



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